

FORM PTO-1440 (REV. 7-80)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 51889/5 US	APPLICATION NO. 10/664,666
INFORMATION DISCLOSURE CITATION		APPLICANT - Douglas R. Hackler, Sr. et al.		
Title: MIM Multilayer Capacitor		FILING DATE- September 18, 2003		

## U.S. PATENT DOCUMENTS

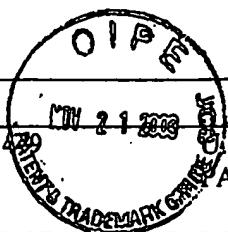
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
G	1	2003/0040161 A1	02/27/03	Schrenk et al.	438	393	09/03/02
	2	2002/0192919 A1	12/19/02	Bothra	438	381	04/26/01
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	4	2002/0047154 A1	04/25/02	Sowlati et al.	257	307	04/07/00
	5	6,524,926 B1	02/25/03	Allman et al.	438	387	11/27/00
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	11	5,912,485	06/15/99	Chao	257	308	10/24/96
	12	5,583,359	12/10/96	Ng et al.	257	306	03/03/95
	13	5,206,787	04/27/93	Fujioka	257	307	03/27/92
	14	5,160,987	11/03/92	Pricer et al.	257	307	02/15/91
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MAY 21 2003

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

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## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	18	03091974 A	17.04.91	Japan				□
	19							
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✓	26	Kim et al., "Development of CVD-Ru/Ta <sub>2</sub> O <sub>5</sub> /CVD-Ru Capacitor with Concave Structure for Multigigabit-scale DRAM Generation," 2001 IEEE, pgs. 12.1.1-12.1.4.
✓	27	Aoki et al., "Robust 130nm-Node Cu Dual Damascene Technology with Low-k Barrier SiCN," 2001 IEEE, pgs. 4.2.1-4.2.4.
✓	28	Samavati et al., "Fractal Capacitors," IEEE Journal of Solid-State Circuits, Vol. 33, No. 12, December 1998, pgs. 2035-2041.
✓	29	Kotecki et al., "(Ba, Sr) TiO dielectrics for future stacked-capacitor DRAM," IBM J. Res. Develop., Vol. 42, No. 3, May 1999, pg. 367-382.
✓	30	Media for SolidState Technology, "Interfacial reaction and thermal stability of Ta <sub>2</sub> O <sub>5</sub> /TiN for metal electrode capacitors," <a href="http://solidstate.articles.printhis.clickability.com/pt/cpt?action=cpt&amp;expire=&amp;urlID=8160">http://solidstate.articles.printhis.clickability.com/pt/cpt?action=cpt&amp;expire=&amp;urlID=8160</a> , 11/4/2003, pgs. 1-7.
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7/1/09

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